



**Advanced Power
Electronics Corp.**

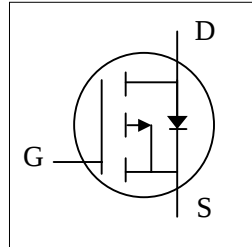
AP4P018M

Halogen-Free Product

P-CHANNEL ENHANCEMENT MODE

POWER MOSFET

- ▼ Low Gate Charge
- ▼ Fast Switching Characteristic
- ▼ Simple Drive Requirement
- ▼ RoHS Compliant & Halogen-Free

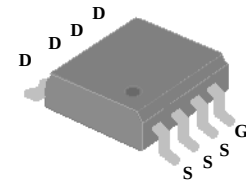


BV_{DSS}	-40V
$R_{DS(ON)}$	18m Ω
I_D^3	-9.4A

Description

AP4P018 series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The SO-8 package is widely preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.



Absolute Maximum Ratings@ $T_J=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ\text{C}$	Drain Current ³ , V_{GS} @ 10V	-9.4	A
$I_D@T_A=70^\circ\text{C}$	Drain Current ³ , V_{GS} @ 10V	-7.5	A
I_{DM}	Pulsed Drain Current ¹	-40	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ³	2.5	W
E_{AS}	Single Pulse Avalanche Energy ⁴	18	mJ
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient ³	50	$^\circ\text{C}/\text{W}$



AP4P018M

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-40	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-9A	-	-	18	mΩ
		V _{GS} =-4.5V, I _D =-6A	-	-	30	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	-	-3	V
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-9A	-	30	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-32V, V _{GS} =0V	-	-	-10	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge	I _D =-6A	-	30	48	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-20V	-	9.5	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	8.5	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =-20V	-	10	-	ns
t _r	Rise Time	I _D =-1A	-	5	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	120	-	ns
t _f	Fall Time	V _{GS} =-10V	-	44	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	3600	5760	pF
C _{oss}	Output Capacitance	V _{DS} =-25V	-	285	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	175	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =-2.1A, V _{GS} =0V	-	-	-1.2	V
t _{rr}	Reverse Recovery Time	I _S =-9A, V _{GS} =0V,	-	21	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=-100A/μs	-	12	-	nC

Notes:

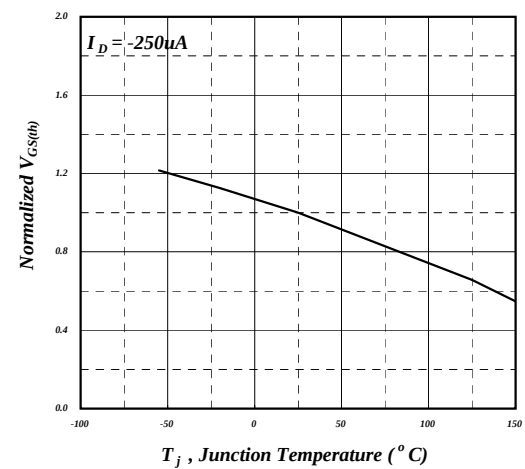
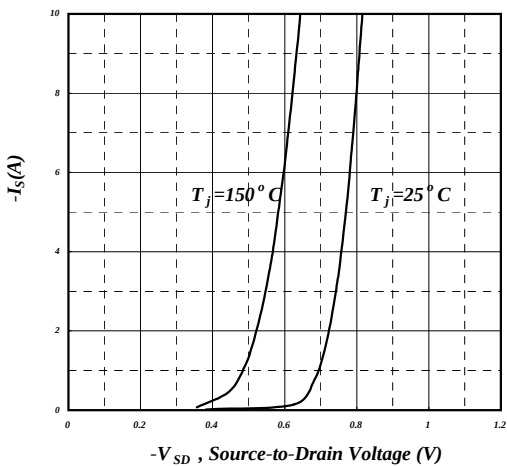
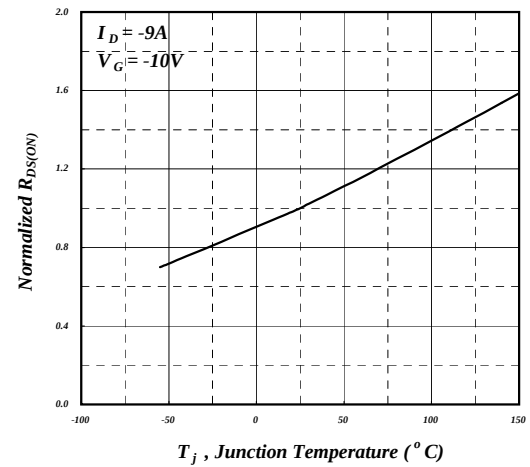
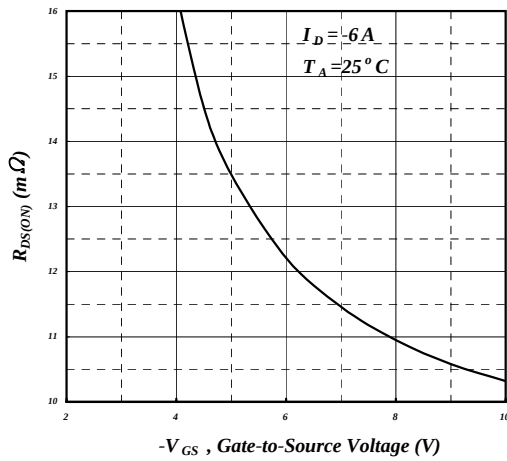
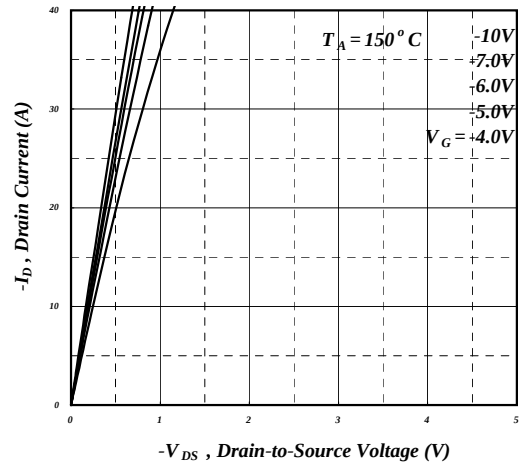
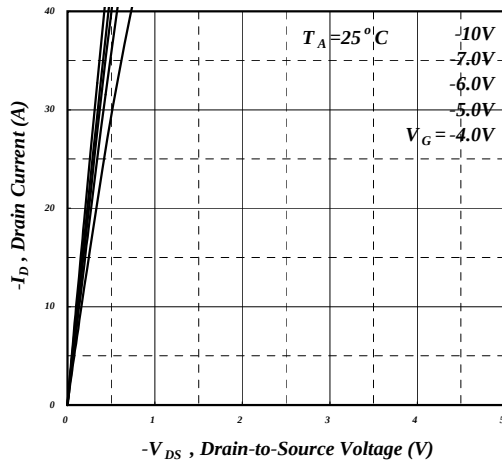
- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board, t ≤ 10s ; 125 °C/W when mounted on Min. copper pad.
- 4.Starting T_j=25°C , V_{DD}=-20V , L=1mH , R_G=25Ω

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

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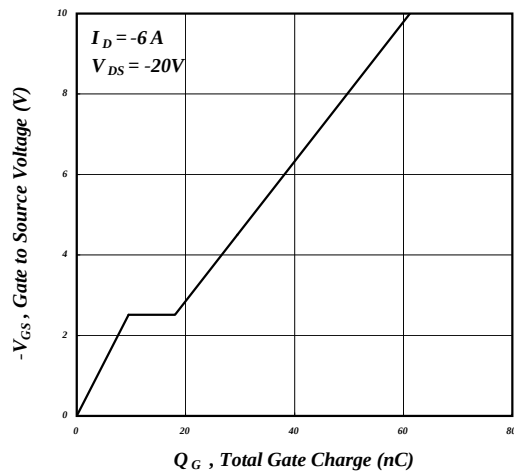


Fig 7. Gate Charge Characteristics

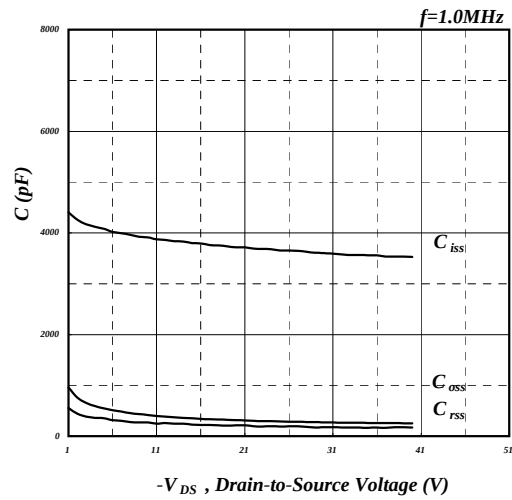


Fig 8. Typical Capacitance Characteristics

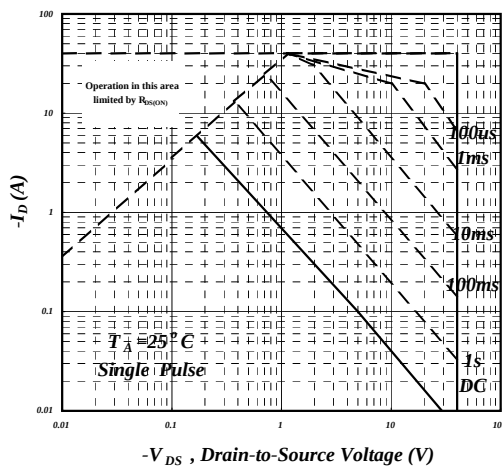


Fig 9. Maximum Safe Operating Area

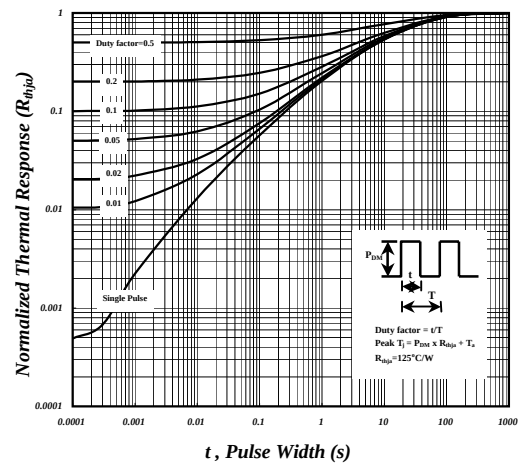


Fig 10. Effective Transient Thermal Impedance

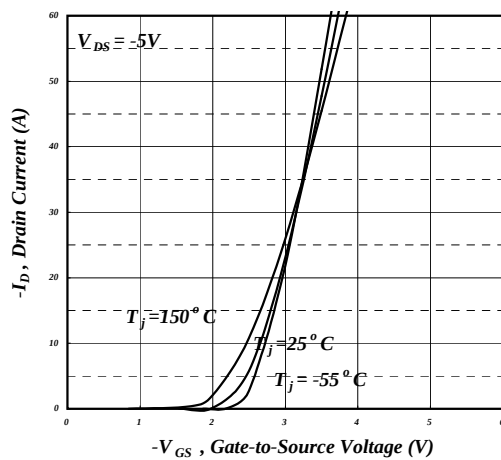


Fig 11. Transfer Characteristics

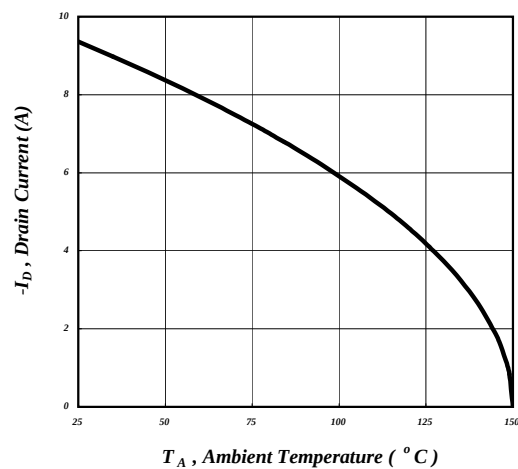


Fig 12. Drain Current v.s. Ambient Temperature

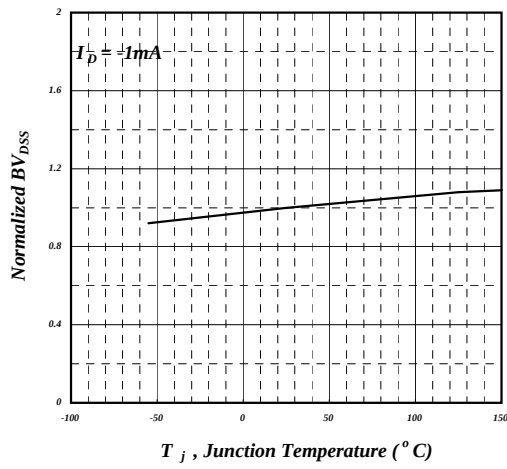


Fig 13. Normalized BV_{DSS} v.s. Junction Temperature

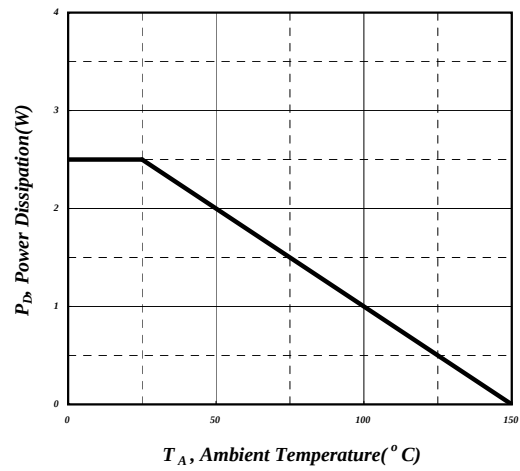


Fig 14. Total Power Dissipation

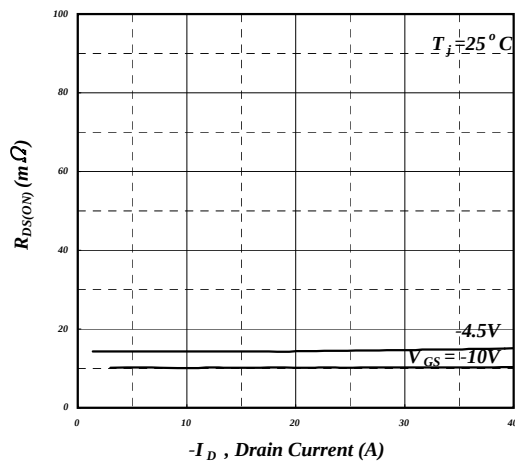
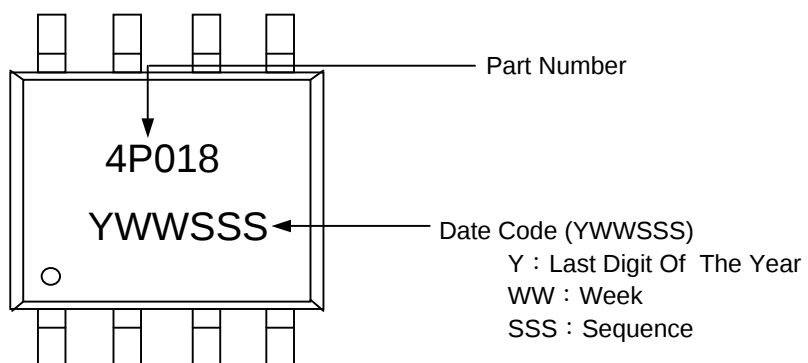


Fig 15. Typ. Drain-Source on State Resistance



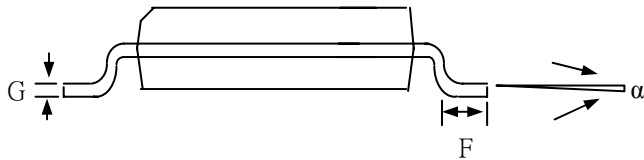
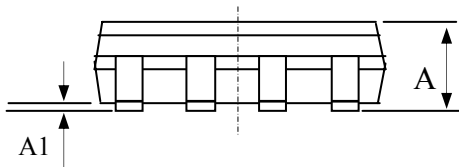
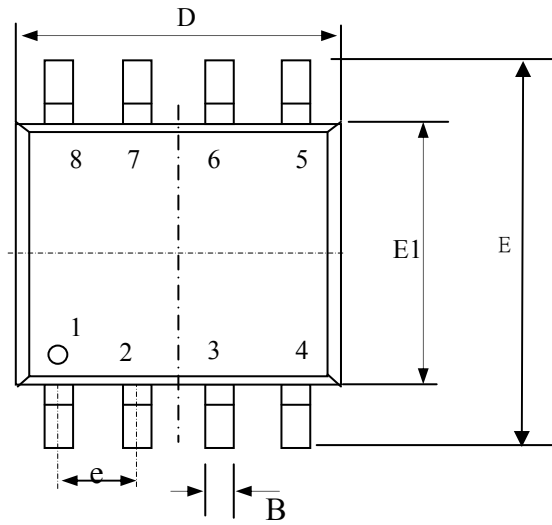
AP4P018M

MARKING INFORMATION





Package Outline : SO-8



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.05	0.15	0.25
B	0.30	0.41	0.51
D	4.80	5.05	5.30
E	5.79	6.00	6.20
E1	3.70	3.90	4.10
e	1.27 TYP		
G	0.17	0.21	0.25
F	0.38	0.83	1.27
α	0°	4°	8°

1.All Dimension Are In Millimeters.

2.Dimension Does Not Include Mold Protrusions.



SO-8 FOOTPRINT :

